SGMNQ25440
40V, Power, Single N-Channel, PDFN Package, MOSFET

FEATURES

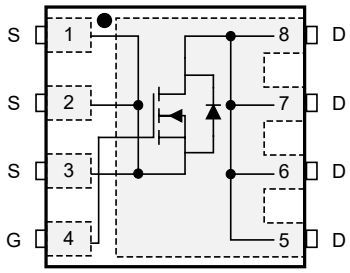
- **Low On-State Resistance**
- **Low Total Gate Charge and Capacitance Losses**
- **Small Footprint (3.3 × 3.3mm^2) for Compact Design**
- **RoHS Compliant and Halogen Free**

PRODUCT SUMMARY

R_{DSON} (TYP) V_{GS} = 10V	R_{DSON} (MAX) V_{GS} = 10V	I_D (MAX) T_C = +25℃
2.1mΩ	2.8mΩ	130A

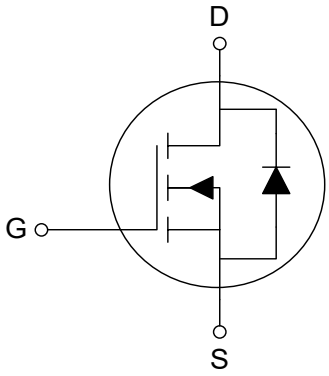
PIN CONFIGURATION

(TOP VIEW)



PDFN-3.3×3.3-8L

EQUIVALENT CIRCUIT



ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	VALUE	UNITS
Drain-to-Source Voltage		V_{DS}	40	V
Gate-to-Source Voltage		V_{GS}	±20	V
Drain Current (1)	T_C = +25℃	I_D	130	A
	T_C = +100℃		83	
	T_A = +25℃		24	
	T_A = +70℃		19	
Drain Current (Pulse) (2)		I_{DM}	470	A
Total Dissipation	T_C = +25℃	P_D	78	W
	T_C = +100℃		31	
	T_A = +25℃		2.2	
	T_A = +70℃		1.4	
Avalanche Current (3)		I_{AS}	49	A
Avalanche Energy (3)		E_{AS}	120	mJ
Junction Temperature		T_J	+150	℃
Storage Temperature Range		T_{STG}	-55 to +150	℃
Lead Temperature (Soldering, 10s)			+260	℃

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

NOTES:

1. The current will be limited by package, PCB, thermal design and operating temperature.
2. t_{PLUSE} < 10μs.
3. Parts are 100% tested at V_{GS} = 10V, I_L = 34.6A, and E_{AS} = 60mJ.

APPLICATIONS

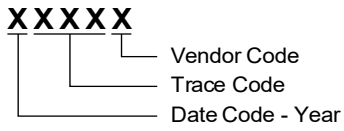
Power Tool
Brushless DC Motor Control
Reverse Battery Protection
DC/DC Converters
Power Load Switch and eFuse
High/Low-Side Switches

PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGMNQ25440	PDFN-3.3×3.3-8L	-55℃ to +150℃	SGMNQ25440TPDB8G/TR	SGM1OF TPDB8 XXXXX	Tape and Reel, 5000

MARKING INFORMATION

NOTE: XXXXX = Date Code, Trace Code and Vendor Code.



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

THERMAL RESISTANCE

PARAMETER	SYMBOL	TYP	UNITS
Junction-to-Ambient Thermal Resistance (1)	$R_{\theta JA}$	56	℃/W
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	1.6	℃/W

NOTE: 1. $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, 2oz copper on FR4 board.

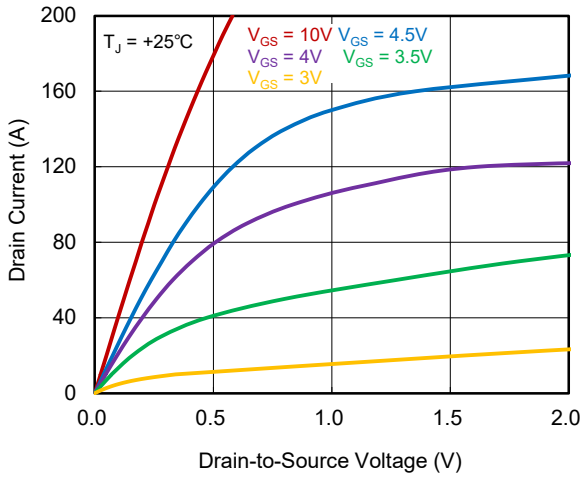
ELECTRICAL CHARACTERISTICS

(T_A = +25℃, unless otherwise noted.)

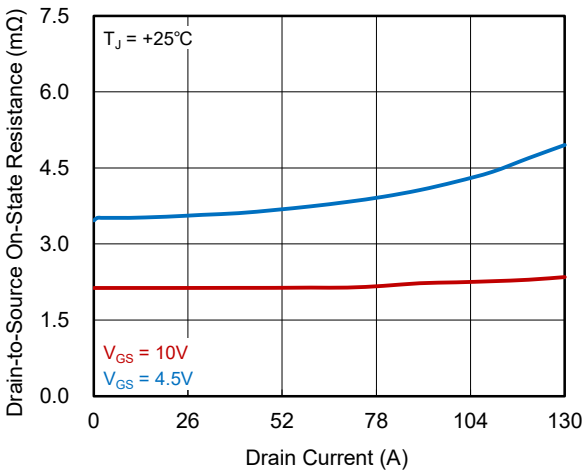
PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Static OFF Characteristics							
Drain-to-Source Breakdown Voltage	V_{BR_DSS}	V_{GS} = 0V, I_D = 250μA		40			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0V, V_{DS} = 32V				10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V				±100	nA
Static ON Characteristics							
Gate-to-Source Threshold Voltage	V_{GS_TH}	V_{GS} = V_{DS}, I_D = 250μA		1.2	1.7	2.5	V
Drain-to-Source On-State Resistance	R_{DSON}	V_{GS} = 10V, I_D = 20A			2.1	2.8	mΩ
		V_{GS} = 4.5V, I_D = 20A			3.5	4.8	
Forward Transconductance	g_{FS}	V_{DS} = 5V, I_D = 20A			33		S
Gate Resistance	R_G	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz			1.3		Ω
Diode Characteristics							
Diode Forward Voltage	V_{FSD}	V_{GS} = 0V, I_S = 20A			0.8	1.2	V
Reverse Recovery Time	t_{RR}	V_{GS} = 0V, I_S = 20A, di/dt = 100A/μs			43		ns
Reverse Recovery Charge	Q_{RR}				34		nC
Dynamic Characteristics							
Input Capacitance	C_{ISS}	V_{GS} = 0V, V_{DS} = 20V, f = 1MHz			1775		pF
Output Capacitance	C_{OSS}				575		
Reverse Transfer Capacitance	C_{RSS}				45		
Total Gate Charge	Q_G	V_{DS} = 20V, I_D = 20A	V_{GS} = 10V		33.9		nC
			V_{GS} = 4.5V		17.3		
Gate-to-Source Charge	Q_{GS}	V_{DS} = 20V, V_{GS} = 4.5V, I_D = 20A			6		
Gate-to-Drain Charge	Q_{GD}				8.3		
Switch Characteristics							
Turn-On Delay Time	t_{D_ON}	V_{GS} = 20V, V_{DS} = 10V, I_D = 20A, R_G = 3Ω			7.2		ns
Rise Time	t_R				26.6		
Turn-Off Delay Time	t_{D_OFF}				24.6		
Fall Time	t_F				7.7		

TYPICAL PERFORMANCE CHARACTERISTICS

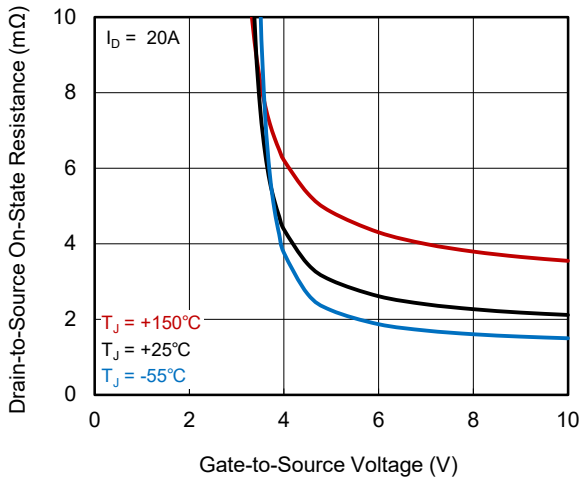
Output Characteristics



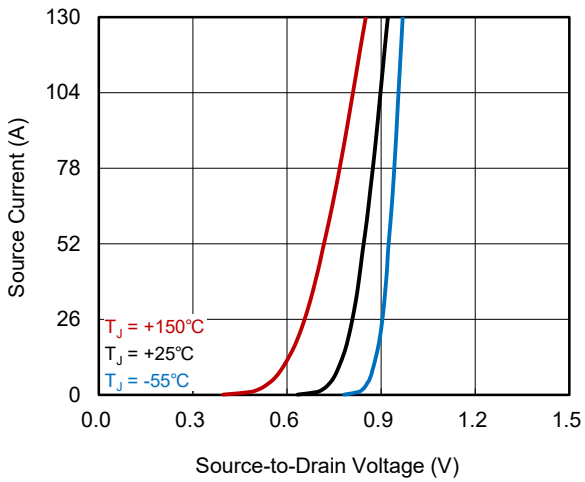
Drain-to-Source On-State Resistance vs. Drain Current



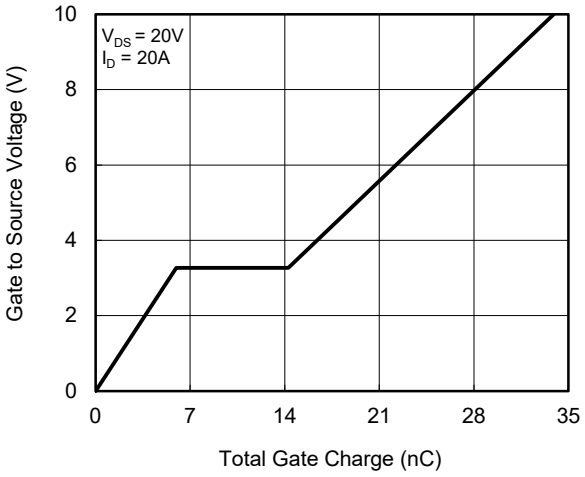
Drain-to-Source On-State Resistance vs. Gate-to-Source Voltage



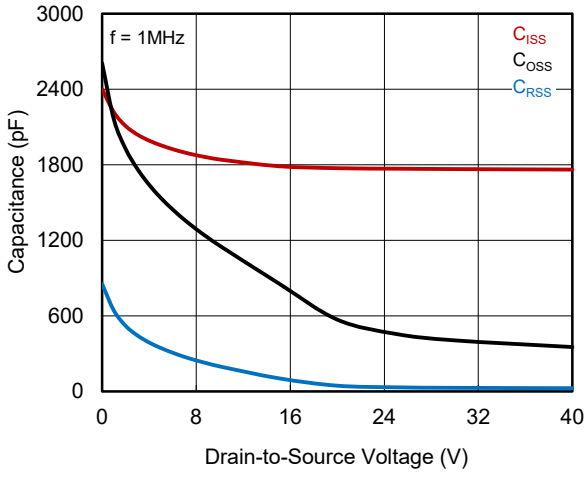
Diode Forward



Gate Charge Characteristics

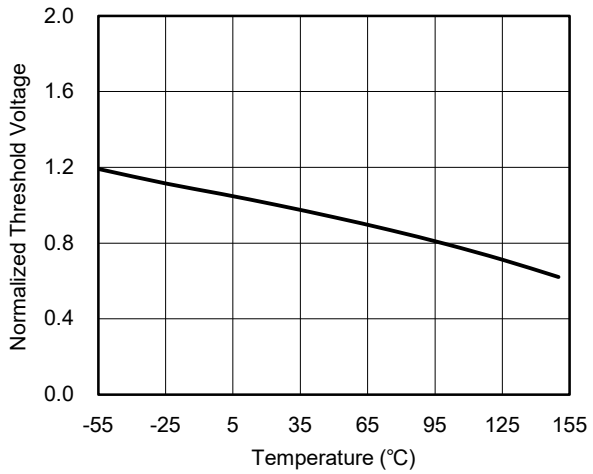


Capacitance Characteristics

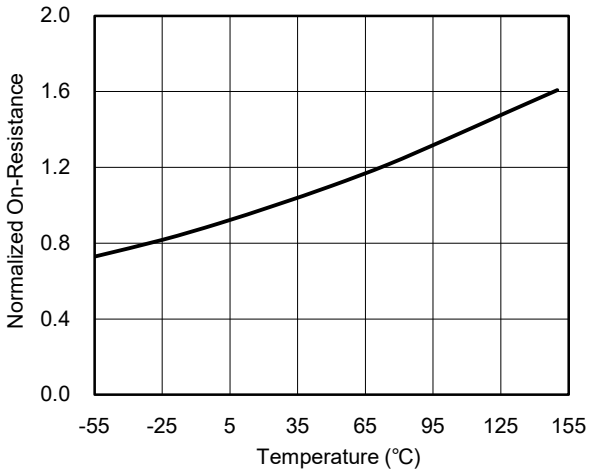


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

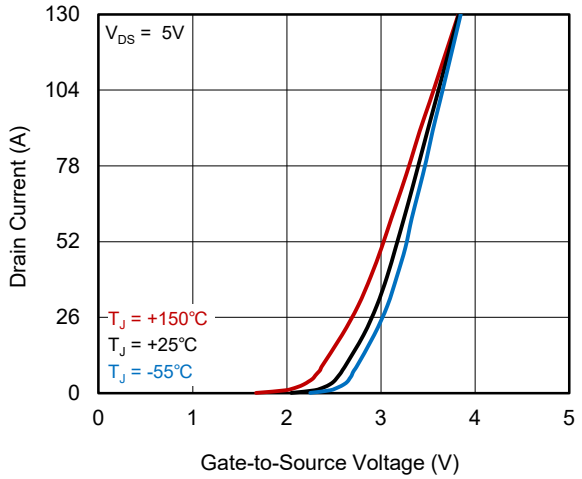
Normalized Threshold Voltage vs. Junction Temperature



Normalized On-Resistance vs. Junction Temperature



Transfer Characteristics



REVISION HISTORY

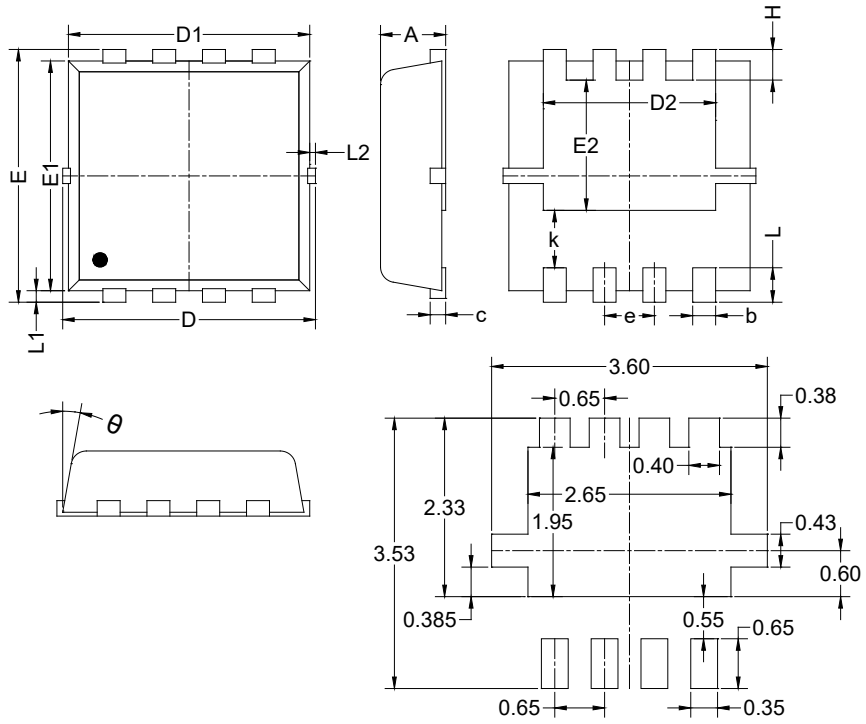
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DECEMBER 2025 – REV.A to REV.A.1	Page
Updated thermal resistance	2

Changes from Original to REV.A (AUGUST 2025)	Page
Changed from product preview to production data	All

PACKAGE OUTLINE DIMENSIONS

PDFN-3.3×3.3-8L



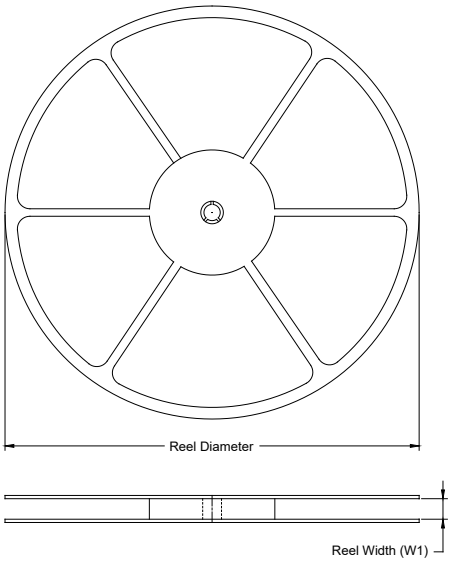
RECOMMENDED LAND PATTERN (Unit: mm)

Symbol	Dimensions In Millimeters		
	MIN	NOM	MAX
A	0.700	-	0.900
b	0.250	-	0.390
c	0.140	-	0.200
D	3.100	-	3.500
D1	3.050	-	3.250
D2	2.150	-	2.350
E	3.100	-	3.500
E1	2.900	-	3.100
E2	1.600	-	1.800
e	0.650 BSC		
H	0.250	-	0.550
k	0.650	-	0.850
L	0.300	-	0.600
L1	0.050	-	0.250
L2	-	-	0.150
θ	8°	-	12°

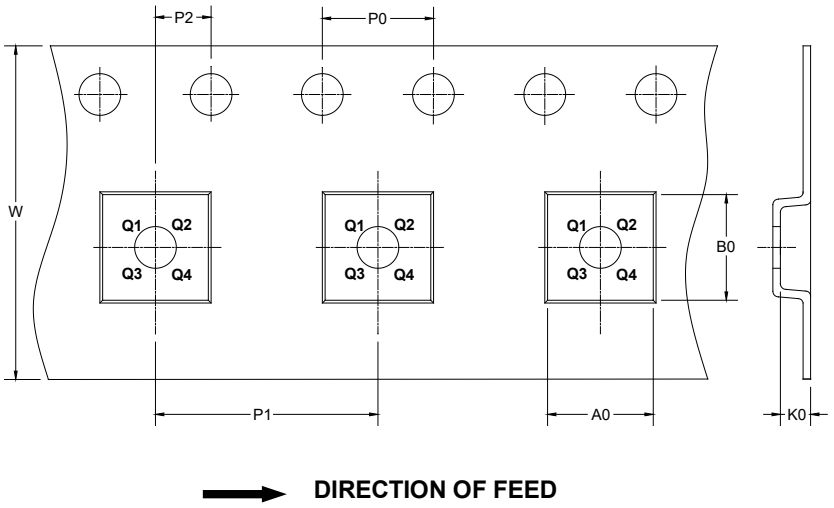
NOTES:
1. This drawing is subject to change without notice.
2. The dimensions do not include mold flashes, protrusions or gate burrs.

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



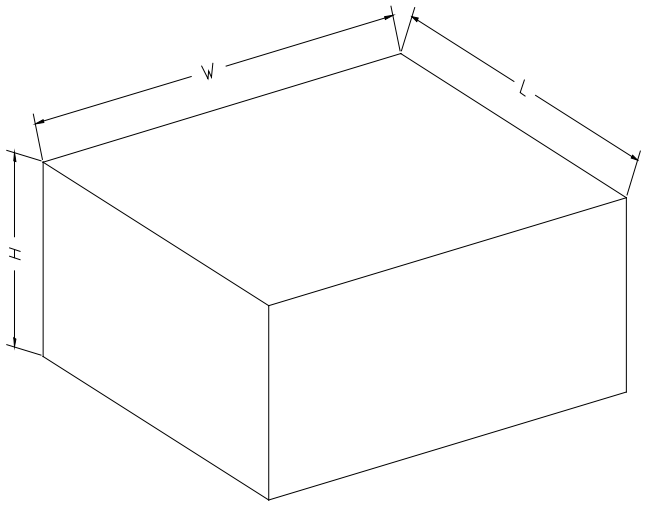
NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
PDFN-3.3×3.3-8L	13"	12.4	3.60	3.60	1.10	4.0	8.0	2.0	12.0	Q1

DD0001

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
13″	386	280	370	5

DD0002